

KSP2222A **NPN General Purpose Amplifier**

July 2006

Features

- Collector-Emitter Voltage: VCEO= 40V
- Collector Power Dissipation: Pc (max)=625mW
- Available as PN2222A



Absolute Maximum Ratings * Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector current	600	mA
T_J	Junction Temperature	+150	°C
T _{stg}	Storage Temperature	-55 ~ +150	°C

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Units
P _C	Collector Power Dissipation, by R _{θJA}	625	mW
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

Electrical Characteristics * Ta = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	75			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{mA}, I_B = 0$	40			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6.0			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 60V, I_{E} = 0$			0.01	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0V, I_{C} = 0$			10	nA
h _{FE}	DC Current Gain	$V_{CE} = 10V, I_{C} = 0.1 \text{mA},$	35			
		$V_{CE} = 10V, I_{C} = 1mA,$	50			
		$V_{CE} = 10V, I_{C} = 10mA,$	75			
		$V_{CE} = 10V, I_{C} = 150mA,$	100		300	
		$V_{CE} = 10V, I_{C} = 500mA,$	40			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$			0.3	V
, ,		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			1	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{mA}, I_B = 15 \text{mA}$		0.6	1.2	V
, ,		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			2.0	V
f _T	Current Gain Bandwidth Product	$I_C = 20$ mA, $V_{CE} = 20$ V, $f = 100$ MHz	300			MHz
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$			8	pF
t _{ON}	Turn On Time	$V_{CC} = 30V, I_{C} = 150mA,$			35	ns
		$I_{B1} = 15 \text{mA}, \ V_{BE(off)} = 0.5 \text{V}$				
t _{OFF}	Turn Off Time	$V_{CC} = 30V, I_{C} = 150mA,$			285	ns
		$I_{B1} = I_{B1} = 15mA$				
NF	Noise Figure	$I_C = 100 \mu A, V_{CE} = 10 V,$			4	dB
		R_S = 1K Ω , f = 1.0KHz				

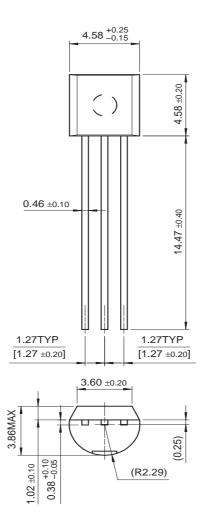
^{*} DC Item are tested by Pulse Test : Pulse Width≤300us, Duty Cycle≤2%

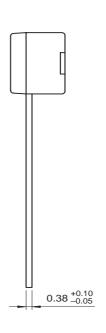
^{* 1.} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Package Dimensions

TO-92





Dimensions in Millimeters

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